

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

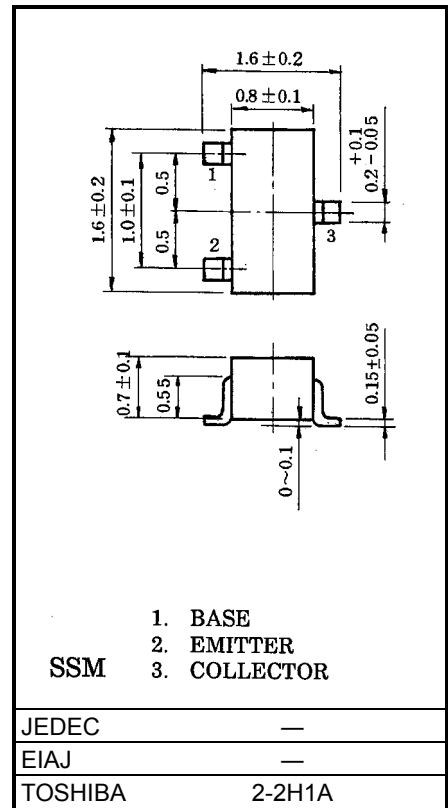
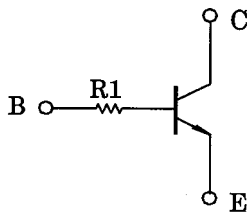
# RN1112,RN1113

Switching, Inverter Circuit, Interface Circuit  
And Driver Circuit Applications

Unit: mm

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2112, RN2113

## Equivalent Circuit

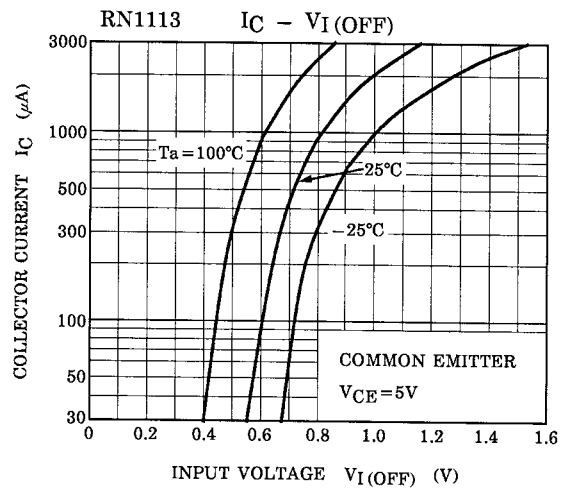
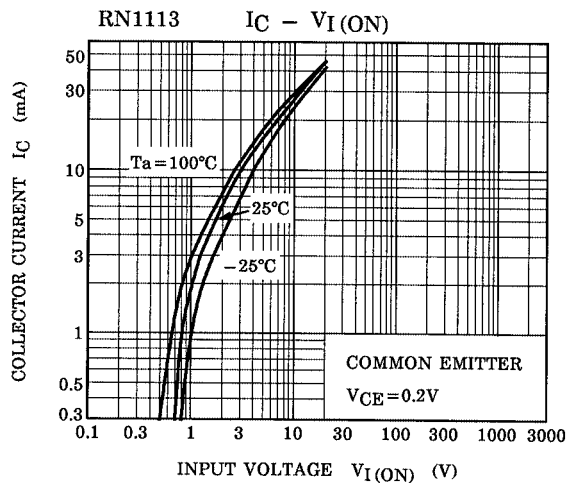
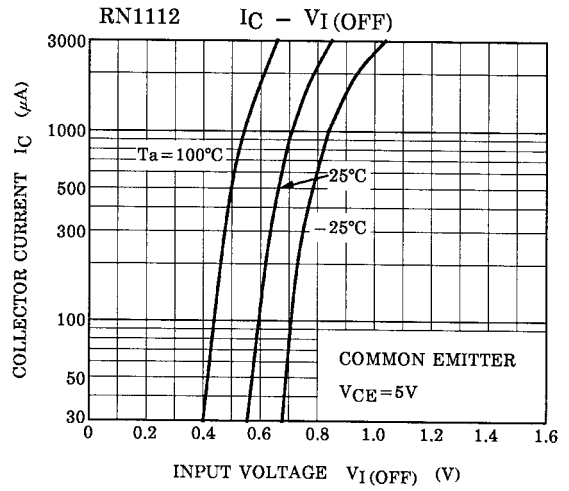
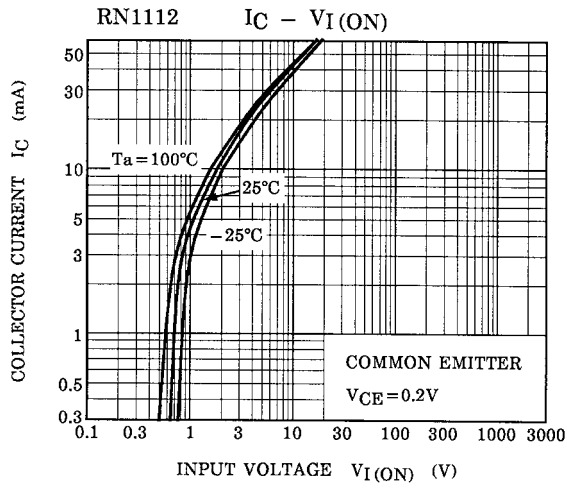


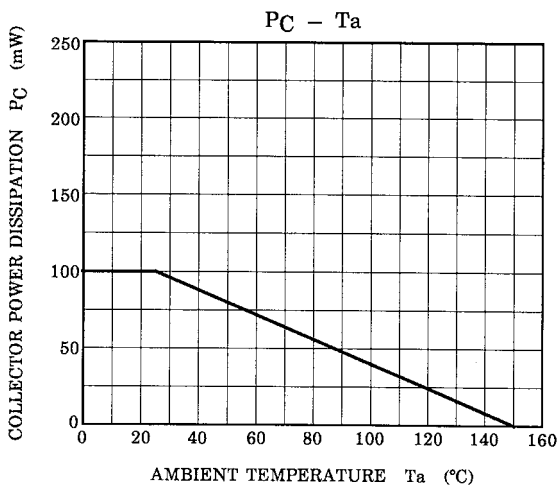
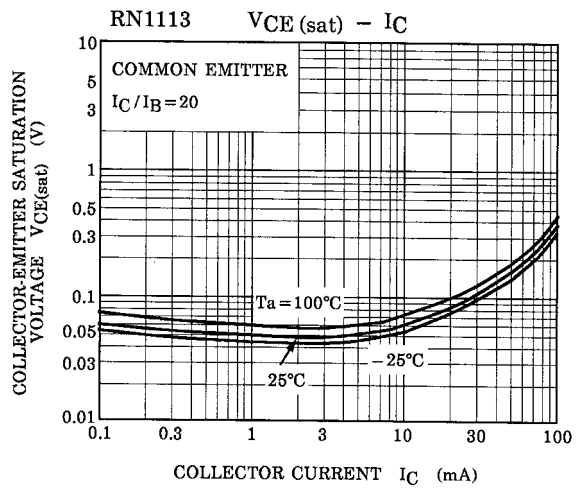
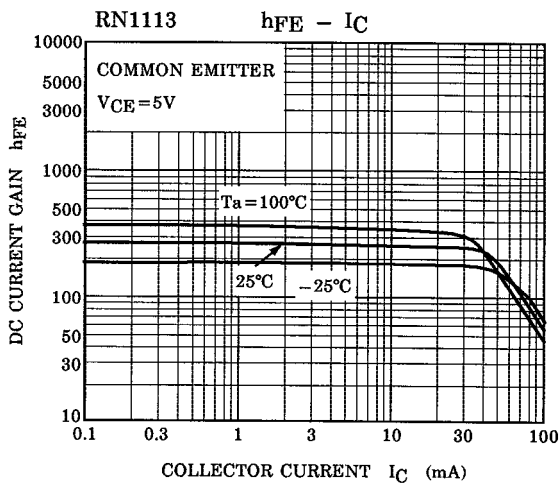
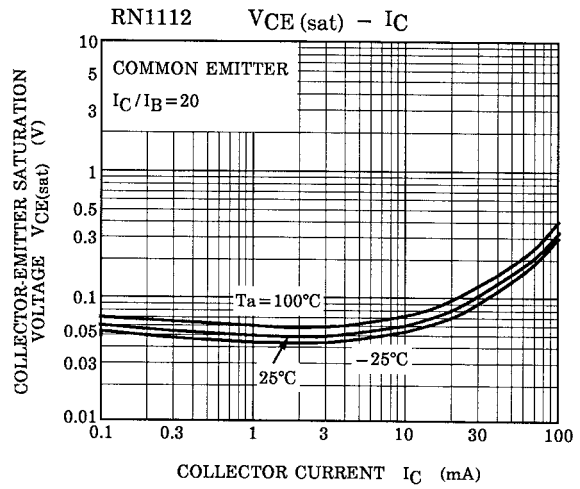
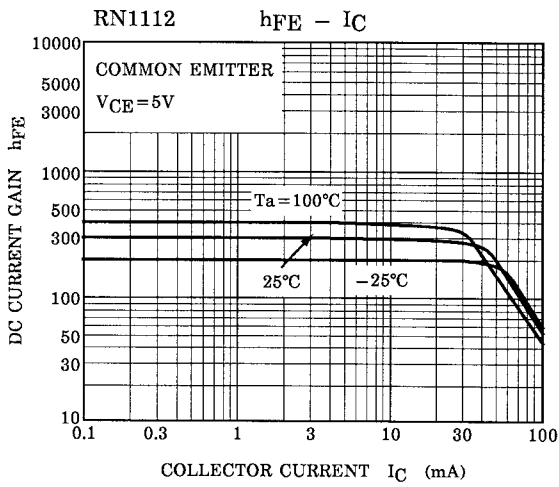
## Maximum Ratings (Ta = 25°C)

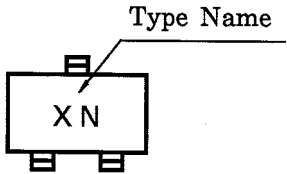
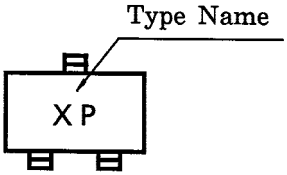
Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>c</sub>	100	mA
Collector power dissipation	P <sub>c</sub>	100	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C

## Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	—	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0	—	—	100	nA
Emitter cut-off current	I <sub>EBO</sub>	—	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	—	—	100	nA
DC current gain	h <sub>FE</sub>	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 1mA	120	—	700	—
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	—	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0.25mA	—	0.1	0.3	V
Transition frequency	f <sub>T</sub>	—	V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA	—	250	—	MHz
Collector output capacitance	C <sub>ob</sub>	—	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz	—	3	6	pF
Input resistor	RN1112	R1	—	15.4	22	28.6	kΩ
	RN1113			32.9	47	61.1	





Type Name	Marking
RN1112	
RN1113	

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